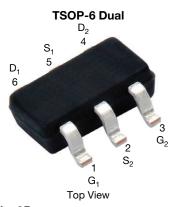


Vishay Siliconix

# Automotive Dual P-Channel 30 V (D-S) 175 °C MOSFET



Marking Code: 9B

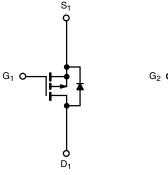
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	-30				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	-0.155				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	-0.300				
I <sub>D</sub> (A)	-2.32				
Configuration	Dual				
Package	TSOP-6				

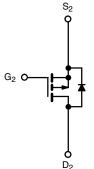
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912









P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		V <sub>DS</sub>	-30	V	
Gate-source voltage		$V_{GS}$	± 20	V	
Continuous drain current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>C</sub> = 25 °C		-2.5		
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	-1.5	A	
Pulsed drain current		I <sub>DM</sub>	-10.2	^	
Continuous source current (diode conduction) a	I <sub>S</sub>	-2.1			
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	PD	1.67	w	
	T <sub>C</sub> = 125 °C	LD LD	0.56	VV	
Unclamped inductive surge UIS		I <sub>AV</sub>	7	A	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Maximum junction-to-ambient <sup>a</sup>	Steady state	R <sub>thJA</sub>	150	°C/W	
Maximum junction-to-foot (drain)	Steady state	R <sub>thJF</sub>	90	C/W	

#### Note

a. Surface mounted on 1" x 1" FR4 board



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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25°C, unless otherwise noted)								
PARAMETER	SYMBOL	T	MIN.	TYP.	MAX.	UNIT		
Static	Static							
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub>	<sub>S</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-0.6	-	-1.5	V	
Gate-body leakage	I <sub>GSS</sub>	$V_{DS}$	$_{S} = 0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
Zero gate voltage drain	_	$V_{GS} = 0 V$	V <sub>DS</sub> = -30 V	-	-	-1		
current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -30 V, T <sub>J</sub> = 55 °C	-	-	-5	μA	
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	V <sub>DS</sub> ≤ -5 V	-4	-	-	Α	
Drain-source on-state	В	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -0.4 A	-	0.140	0.155	Ω	
resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -0.2 A	-	0.265	0.300		
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = -5 V, I <sub>D</sub> = -1 A		-	2.2	-	S	
Diode forward voltage a	$V_{SD}$	I <sub>S</sub> = -0.5 A, V <sub>GS</sub> = 0 V		-	-0.83	-1.1	V	
Dynamic <sup>b</sup>								
Total gate charge	$Q_g$			-	8.6	11.1		
Gate-source charge	$Q_{gs}$	$V_{GS} = -10 \text{ V}$	$V_{DS} = -15 \text{ V}, I_{D} = -3 \text{ A}$	-	1.2	-	nC	
Gate-drain charge	$Q_{gd}$			-	3	-		
Gate resistance	$R_g$	f = 1 MHz		2.5	-	7.2	Ω	
Turn-on delay time	t <sub>d(on)</sub>			-	5.7	8		
Rise time	t <sub>r</sub>	$V_{DD}$ = -10 V, $R_L$ = 10 $\Omega$ $I_D \cong$ -1 A, $V_{GEN}$ = -10 V, $R_g$ = 1 k $\Omega$		-	3	4	]	
Turn-off delay time	t <sub>d(off)</sub>			-	13.8	18	ns	
Fall time	t <sub>f</sub>			-	2	3	1	

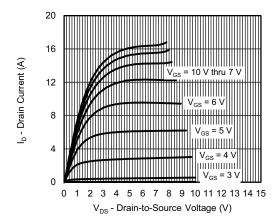
#### **Notes**

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing

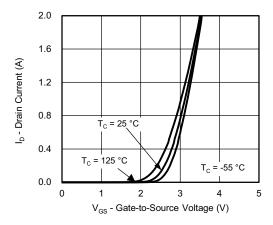
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



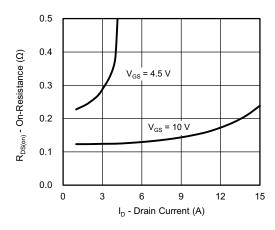
#### TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



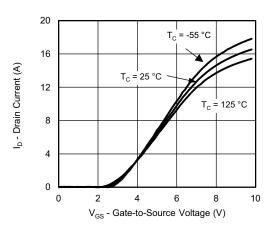
#### **Output Characteristics**



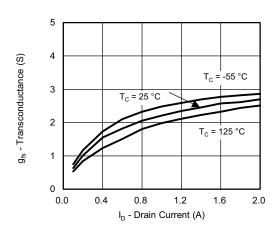
**Transfer Characteristics** 



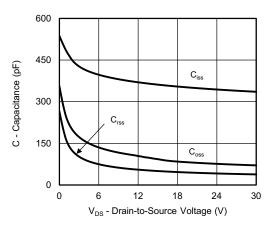
On-Resistance vs. Drain Current



**Transfer Characteristics** 



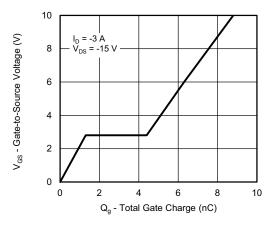
Transconductance



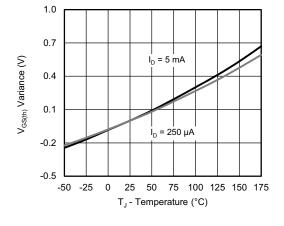
Capacitance



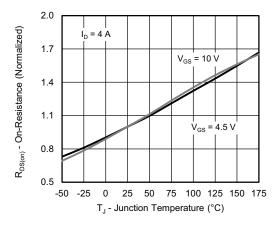
## TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



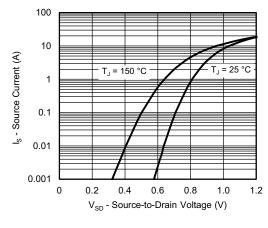
**Gate Charge** 



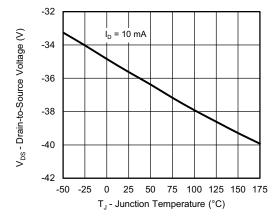
Threshold Voltage



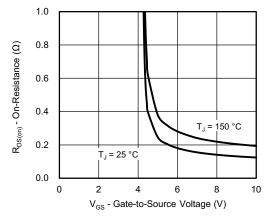
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



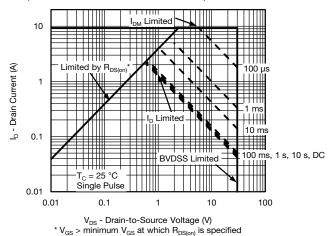
Drain Source Breakdown vs. Junction Temperature



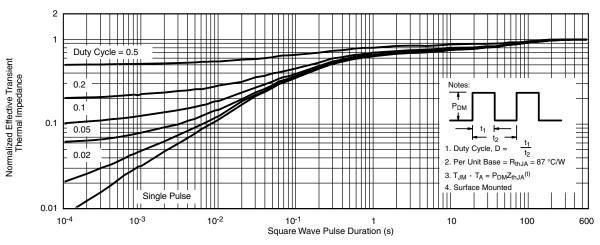
On-Resistance vs. Gate-to-Source Voltage



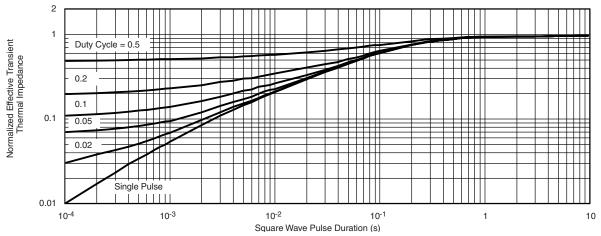
## TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

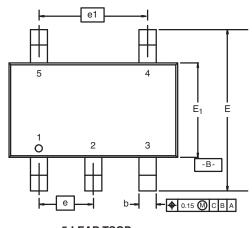
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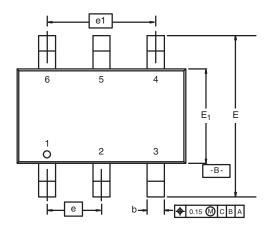




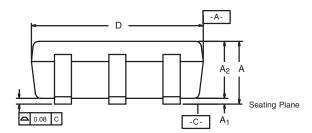
TSOP: 5/6-LEAD

**JEDEC Part Number: MO-193C** 

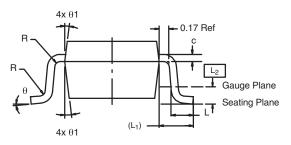




**5-LEAD TSOP** 







	MILLIMETERS			ı	NCHES	
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	-	1.10	0.036	-	0.043
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067
е	0.95 BSC			0.0374 BSC		
e <sub>1</sub>	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L <sub>1</sub>	0.60 Ref				0.024 Ref	
L <sub>2</sub>	0.25 BSC				0.010 BSC	
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
$\theta_1$	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540						

Document Number: 71200

18-Dec-06

# VISHAY.

#### **RECOMMENDED MINIMUM PADS FOR TSOP-6**



Recommended Minimum Pads Dimensions in Inches/(mm)

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